Abstracts

Quasi-Monolithic 4-GHz Power Amplifiers with 65-Percent Power-Added Efficiency

B.D. Geller and P.E. Goettle. "Quasi-Monolithic 4-GHz Power Amplifiers with 65-Percent Power-Added Efficiency." 1988 MTT-S International Microwave Symposium Digest 88.2 (1988 Vol. II [MWSYM]): 835-838.

A highly miniaturized C-band 1-W GaAs FET amplifier, part of a three stage power amplifier for communications satellite applications, has been designed, fabricated, and tested. It achieves a maximum power-added efficiency of 65 percent, and occupies an area of 0.20 x 0.36 in. The circuit employs a low-reactance termination at the second harmonic and low-loss quasi-monolithic circuitry. These results were obtained on the first fabrication run and with no circuit tuning.

❑ Return to main document.